

MARKED-UP VERSION OF THE CLAIMS:

18. (Amended) A trench capacitor comprising:

a crystalline silicon substrate including deep trenches having surfaces in the substrate substantially free of native oxide; and

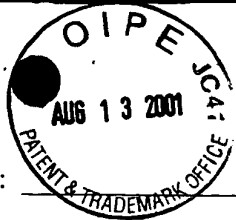
a dielectric stack, including a continuous monocrystalline silicon nitride layer, formed on the surfaces of the trenches, the dielectric stack for forming a node dielectric between electrodes of the trench capacitor.

23. (Amended) A trench capacitor comprising:

a crystalline silicon substrate including a trench having a surface formed in the substrate, the surface being substantially free of native oxide;

a continuous monocrystalline silicon nitride layer, formed on the surface of the trench; and

an amorphous silicon nitride layer formed on the crystalline silicon nitride layer, the crystalline silicon nitride layer and the amorphous silicon nitride layer for forming a dielectric between electrodes.



PATENT

GAU 2812

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Washington, D.C. 20231
Box PATENT APPLICATION

09/594,638

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Sir:

Transmitted herewith is an amendment in the identified application noted below.

☒ No additional fee is required.

In re application of:

Serial No.: Jammy et al.

Filed: June 15, 2000

For: **METHOD FOR FORMING CRYSTALLINE SILICON NITRIDE**

The filing fee has been calculated as shown below:

	(Col. 1)	(Col. 2)	(Col. 3)	OTHER THAN A SMALL ENTITY FEE	
CLAIMS	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST NO. PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE	ADDIT. FEE
TOTAL	<u>12</u>	MINUS <u>12</u>	= <u>20</u>	x 18 =	\$ <u>0</u>
INDEP	<u>3</u>	MINUS <u>3</u>	= <u>20</u>	x 18 =	\$ <u>0</u>
FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM				+ 270 =	\$0
TOTAL					\$ <u>0</u>

☒ Please charge my Deposit Account No. 19-2179 in the amount of \$0

A duplicate copy of this sheet is enclosed.

A check in the amount of \$_____ is attached.

☒ The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 19-2179.


A duplicate copy of this sheet is enclosed.

☒ Any additional filing fees required under 37 CFR 1.16 for the presentation of excess claims.

☒ Any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

Date: 8/8/01


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